

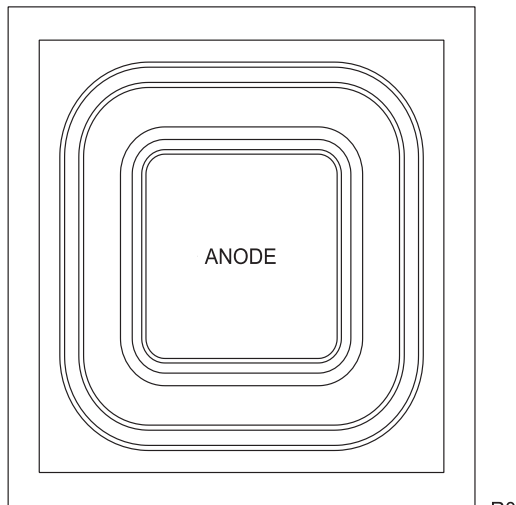
PROCESS CPD80V
Switching Diode
High Voltage Switching Diode Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	16 x 16 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	6.5 x 6.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au-As - 13,000Å

GEOMETRY



BACKSIDE CATHODE

GROSS DIE PER 5 INCH WAFER

64,704

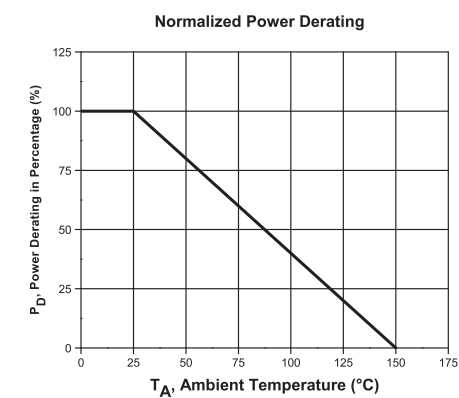
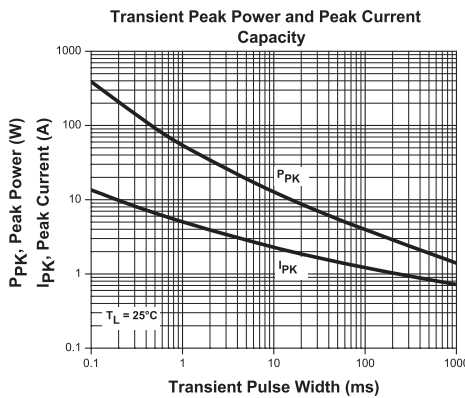
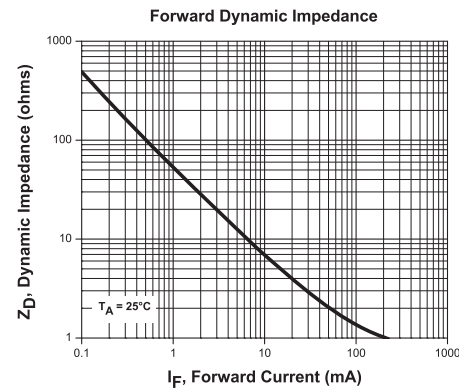
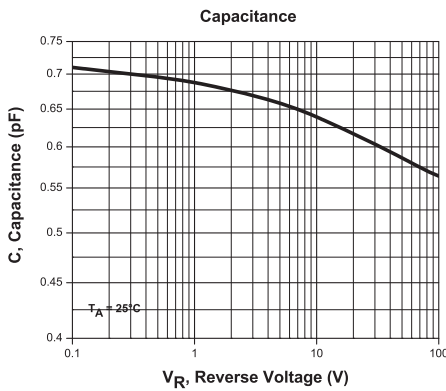
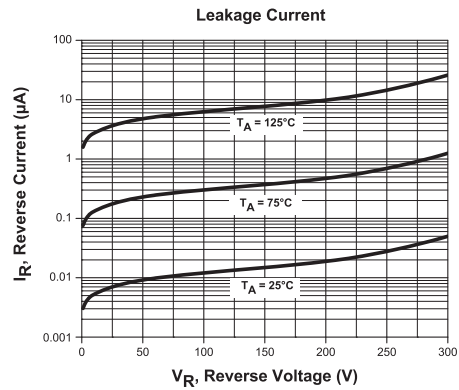
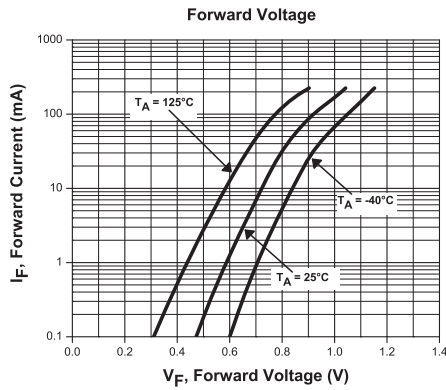
PRINCIPAL DEVICE TYPES

- CMPD2003
- CMPD2004
- CMPD2005
- 1N3070
- CMDD2004
- CMSD2004
- CMOD2004
- CMXD2004
- CMLD2004

R3 (22-March 2010)

PROCESS CPD80V

Typical Electrical Characteristics



R3 (22-March 2010)